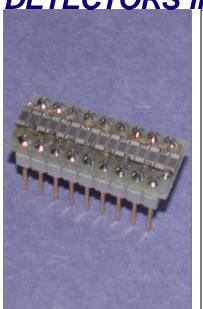
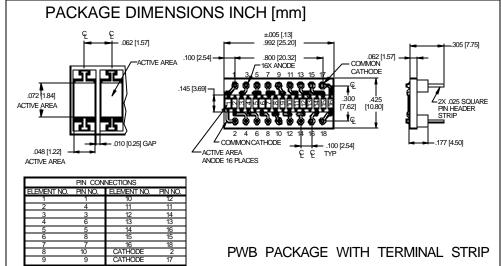
PHOTONIC DETECTORS INC.

Silicon Photodiode Array, Photovoltaic 16 element Type PDB-V216





FEATURES

- .062 inch centers
- Stackable
- Blue enhanced
- Low cost

DESCRIPTION

The **PDB-V216** is a common cathode, monolithic silicon PIN photodiode linear array. Designed to be stacked end to end to form a line of pixels. Plugable into Mill-Max or 3M terminal receptacles.

ACTIVE AREA = 2.31mm²

APPLICATIONS

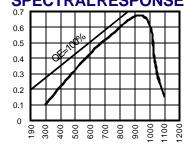
- Cardreader
- Scanners
- Characterrecognition

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
$V_{\mathtt{BR}}$	Reverse Voltage		50	V
T _{STG}	Storage Temperature	-40	+100	⊙C
T _o	Operating Temperature Range	-20	+75	⊙C
T _s	Soldering Temperature*		+265	∘C
IL	Light Current		0.5	mA

^{*1/16} inch from case for 3 secs max

SPECTRALRESPONSE



RESPONSIVITY (A/W)

WAVELENGTH(nm)

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
l _{sc}	Short Circuit Current	H = 100 fc, 2850 K	18	28		μΑ
I _D	Dark Current	$H = 0, V_R = 1 V$		1.0	5.0	nA
R _{SH}	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$	200	400		MΩ
TCR _{SH}	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		%/℃
C _J	Junction Capacitance	$H = 0, V_R = 0 V^{**}$		300	400	pF
λrange	Spectral Application Range	Spot Scan	350		1100	nm
λр	Spectral Response - Peak	Spot Scan		950		nm
V _{BR}	Breakdown Voltage	Ι = 10 μΑ	15	30		V
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		2x10 ⁻¹⁴		W/ √ Hz
tr	Response Time	$RL = 50 \Omega V_R = 10 V$		50		nS